AW306A Datasheet

Zhuhai Jieli Technology Co.,LTD

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AW306A Features

CPU

- 32-bit DSP
- with IEEE754 Single precision FPU
- Icache
- 64Vectored interrupts
- 8 Levels interrupt priority
- Mathematic alaccelerate engine
- Support EMU

Memory

- On-chip SRAM (include cache)
- On-chip ROM
- Built-In Flash
- 4 region MPU protects

Clocks

- On-chip 16 MHz clock oscillator
- On-chip 200 kHz lower-temperature-drift clock oscillator
- 24 MHz crystal oscillator
- 32.768KHz crystal oscillator

Audio

- One channel 16-bit DAC,SNR maximum 91dB
- One channel 16-bit ADC,SNR maximum 95dB
- One channel 16-bit APA, SNR maximum 99dB
- Audio DAC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32kHz/44.1kHz/48kHz are supported
- Audio ADC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32 kHz/44.1kHz/48kHz are supported
- AUDIO ADC Support one analog MIC, supports single-end or differential MIC/LINEIN input
- Supported digital MIC inputs(IIS Port)
- Audio DAC supports single-ended mode, need connect PA to drive speaker

Audio APA

- Mono Class-D Speaker Amplifier
- Use PWM modulation technique, support 32/44.1/48kHz sample rate
- support single-end or differential output to drive 4 or 8 ohm speaker directly.

Bluetooth

- Compliant with Bluetooth V5.4+BLE specification (QDID:222830)
- Support AoA TX direction finding
- Meet class2 and class3 transmitting power requirement
- Maximum +6dbm transmitting power
- BLE receiver with minimum -98dBm sensitivity
- bap 1.0\pacs 1.0\ccp 1.0\mcp 1.0\micp 1.0\vcp 1.0\csip 1.0

LP Touch

8-channel LP Touch with low power wakeup

Peripherals

- One full speed USB OTG controller
- One SD host controller for eMMC/SD
- Four multi-function 32-bit timers, support capture and PWM mode
- Three UART interface
- I2C Master/Slave interface
- Three SPI Master/Slave interface
- I2S AUDIO Master/Slave interface
- 9-channel 12-bit ADC for analog sampling
- One CAN interface
- 25 Individually programmable and multiplexed GPIO pins
- Support IO function remapping
- Up to 25 external interrupt/wake-up source(low power available,can be multiplexed to any I/O)



PMU

Built-in LDO

Minimum 3uA current consumption in the soft-off mode

RTC with 32.768k osc

VPWR range: 1.8V to 5.5V

IOVDD range: 2.2V to 3.4V

Packages

QFN32 (4mm*4mm)

Temperature

• Operating temperature: -40°C to +85°C

Storage temperature: -65°C to +150°C

Applications

Bluetooth intercom

Bluetooth TV remote controls





1 Block Diagram

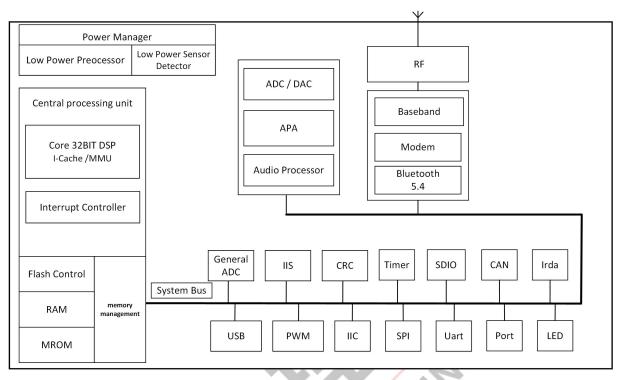


Figure 1-1 AW306A Block Diagram



2 Pin Definition

2.1 Pin Assignment

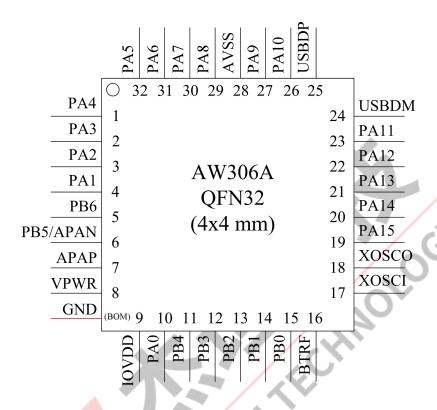


Figure 2-1 AW306A Package Diagram



2.2 Pin Description

Table 2-1 AW306A Pin Description

PIN	Name	Туре	Function	Other Function				
NO.	Ivaille	Туре	runction	Other Function				
				ADC0: ADC Input Channel0				
				AIN_AP1: audio adc differential input AP1				
1	PA4	I/O	GPIO	MCPWM_L0				
1	1 A T	1/0	GI IO	ALNK_DAT1A				
				SPI2DIA				
				UART2RXA				
				Touch2				
				TMR3				
2	PA3	I/O	GPIO	MCPWM_H0				
2	1713	1.0	GI IO	ALNK_DAT0A				
				SPIDOC				
				UART2TXA				
			*	Touch1				
		I/O		Long-press reset				
			GPIO	TMR2				
3	PA2		(pull up)	PWM1				
				ALNK_MCLKA				
				SPIICLKC				
				UARTIRXC				
		4		Touch0				
				LVD				
4	PA1	I/O	GPIO	TMR1				
	IAI	1/0	GI IO	PWM0				
		The same		SPIIDIC				
				UARTITXC				
		*/-	GPIO					
5	PB6	I/O	(High Voltage Resistant)					
		The same of the sa	GPIO	ALNK_DAT1B				
	PB5 I/O		(High Voltage Resistant)	SPI2DIB				
6			(111gii voitage Resistalit)	UARTIRXB				
	APAN	AO		APA differential output N				
7	APAP	AO		APA differential output P				
8	VPWR	P		Power supply 5v				
9	IOVDD	Р		IO Power 3.3v				



			GPIO	TMDO				
10	10 PA0 I/O (pull down)		(pull down)	TMR0 PWM2				
			(High Voltage Resistant)	P WIMZ				
				Touch7				
11	PB4	I/O	GPIO	MCPWM_L2				
11	1 1 1 1 1	1/0	GI 10	ALNK_DAT0B				
				UARTITXB				
12	PB3	I/O	GPIO	Touch6MCPWM_H2				
				Touch5				
13	PB2	I/O	GPIO	OSCO_32K				
				SPI2D3				
				Touch4				
14	PB1	I/O	GPIO	OSCI_32K				
				MCPWM_TMR2CK				
				Touch3				
				MCLR MCPWM TMR1CK				
			GPIO	PWM3				
15	PB0	30 I/O	(pull up)	UART1 RTS				
			(fF)	SPI1DOA				
				UARTOTXB				
				SD0CLKB				
16	BTRF	RF		Bluetooth RF antenna				
17	XOSCI	I		Crystal Oscillator Input;				
18	XOSCO	0		Crystal Oscillator Output;				
		1		ADC5: ADC Input Channel5				
		1		MCPWM_TMR0CK				
10	D. 4.5	7.10		SPI0DIB1				
19	PA15	I/O	GPIO	SPICLKA				
		1		UARTIRXA				
		A		SD0CMDB				
		May "	1	ADC4: ADC Input Channel4				
		100		MCPWM_FPIN2				
20	PA14	I/O	GPIO	SPI0DOB0				
20	IAIT	1/0	GI 10	SPI1DIA				
				UARTITXA				
				SD0DAT0B				
				ADC3: ADC Input Channel3				
				MCPWM_FPIN1				
21	PA13	I/O	GPIO	MCPWM_L1				
				SPIOCLKB				
				SPI1D3				



				ADC differential input N			
				MCPWM_FPIN0			
22	PA12	I/O	GPIO	MCPWM_H1			
22	17112	1/0	GI IO	SPI0DATB3			
				SPI1D2			
				ADC differential input P			
				CLKOUT2			
23	PA11	I/O	GPIO	SPI0DATB2			
23	IAII	1/0	GI IO	SPI2DOC			
				UART2RXC			
				ADC6: ADC Input Channel6			
24	HCDDM	I/O	GPIO	High Speed USB Data Minus			
24	USBDM	1/0	(pull down)	IIC_SDA_A			
				SPI2DOB			
				UARTIRXD			
				ADC6: ADC Input Channel6			
2.5	HGDDD	1/0	GPIO (pull down)	High Speed USB Data Positive			
25	USBDP	I/O		IIC_SCL_A			
				SPI2CLKB			
				UARTITXD			
				CLKOUTI			
26	PA10	I/O	GPIO	SPI0DATA3			
				SPI2CLKC			
				UART2TXC			
		3		CLKOUT0			
27	PA9	I/O	GPIO	ALNK_MCLKB			
		7 1		SPI0DATA2			
				SPI2DIC			
28	AVSS	G		AUDIO Ground			
		1		ADC2: ADC Input Channel2			
29	29 PA8 I/O GPIO		GPIO	AIN_AP0: audio adc differential input AP0			
		A		ALNK_LRCKA			
			3	UART2RXB			
				AIN_AP4: audio adc differential input AP4			
30	PA7	I/O	GPIO	MIC_BIASCAP1			
	11/			ALNK_SCLKA			
				UART2TXB			



				AIN_AP3: audio adc differential input AP3
				AIN_AN: audio adc differential input N
				CAP0
31	DAC	1/0	CDIO	UART1_CTS
31	PA6	I/O	GPIO	IIC_SDA_D
				ALNK_DAT3A
				SPI2DOA
				UART0RXA
				ADC1: ADC Input Channel1
				AIN_AP2: audio adc differential input AP2
				DAC: Digital-to-Analog Converter output channel
32	PA5	I/O	GPIO	IIC_SCL_D
				ALNK_DAT2A
				SPI2CLKA
				UART0TXA
BOM	GND	G		Ground;

Note: Timer IIC ALNK SPI UART SD CAN function can be remapped to any I/O

Pin Type	Description	Pin Type	Description
P	Power	I/O	Input or Output
PO	Power Output	ľ	Input
PI	Power Input	0	Output
G	Ground	RF	RF antenna
AO	Analog Output		

3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1

Parameter	Min	Max	Unit
Operating temperature	-40	+85	°C
Storage temperature	-65	+150	°C
Supply Voltage	-0.3	6	V
Voltage applied at IOVDD	-0.3	3.6	V
Voltage applied to GPIO(Except PA0 /PB5/PB6)	-0.3	3.6	V
Voltage applied to High Voltage Resistant IO (PA0/PB5/PB6)	-0.3	5.5	V
	Operating temperature Storage temperature Supply Voltage Voltage applied at IOVDD Voltage applied to GPIO(Except PA0 /PB5/PB6)	Operating temperature -40 Storage temperature -65 Supply Voltage -0.3 Voltage applied at IOVDD -0.3 Voltage applied to GPIO(Except PA0 /PB5/PB6) -0.3 Voltage applied to High Voltage Resistant IO -0.3	Operating temperature -40 +85 Storage temperature -65 +150 Supply Voltage -0.3 6 Voltage applied at IOVDD -0.3 3.6 Voltage applied to GPIO(Except PA0 /PB5/PB6) -0.3 3.6 Voltage applied to High Voltage Resistant IO -0.3 5.5

Note: The chip can be damaged by any stress in excess of the absolute maximum ratings listed below



3.2 PMU Characteristics

Table 3-2

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions			
VPWR	Voltage Input	1.8	1	5.5	V				
Operating mo	Operating mode								
IOVDD	Voltage output	-	3.0	_	V	VPWR = 3.3V, 10mA loading			
IOVDD	Loading current	1	1	120	mA	IOVDD=3.0V@VPWR=3.3V			
Low Power n	Low Power mode								
IOVDD	Loading current	-	-	20	mA	IOVDD=3.2V@VPWR=3.7V			

3.3 IO Input/Output Electrical Logical Characteristics

Table 3-3

GPIO (Exc	GPIO (Except PA0/PB5/PB6) input characteristics									
Symbol	Parameter	Min		Тур	Max	Unit	Test Conditions			
V_{IL}	Low-Level Input Voltage	-(0.3	_	1.4	V	IOVDD = 3.2V			
V_{IH}	High-Level Input Voltage	1	.8		3.6	V	IOVDD = 3.2V			
High Voltag	ge Resistant IO (PA0/P	B5/PB	6) input	character	ristics	K.				
Symbol	Parameter	M	lin	Тур	Max	Unit	Test Conditions			
V _{IL}	Low-Level Input Voltage	-().3	-/	1.4	V	IOVDD = 3.2V			
V_{IH}	High-Level Input Voltage	1.8		/-	5.5	V	IOVDD = 3.2V			
GPIO & Hi	gh Volta <mark>ge Resi</mark> stant I	O outp	ut chara	acteristics						
Symbol	Parameter		G	PIO	Тур	Unit	Test Conditions			
$ m V_{OL}$	Vol. 0.1* IOVDD Drive current		PA1~PA15 PB0~PB4 PA0, PB5, PB6		HD=0:-3 HD=1:-8 HD=2:-20 HD=3:-40~-50	mA	IOVDD = 3.2V			
			USBDM USBDP		-8					
Var	0.9* IOVDD Drive current		PA1~PA15 PB0~PB4		HD=0:3 HD=1:8 HD=2:20 HD=3:40~50	mA	IOVDD = 3.2V			
$ m V_{OH}$			PAO、PB5、PB6 USBDM USBDP		8	mA	10 v DD — 3.2 v			



3.4 Internal Resistor Characteristics

Table 3-4

Port	Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment		
PA0~PA15 PB0~PB6	PU=0: NC PU=1: 10K PU=2: 100K PU=3: 1M	PD=0: NC PD=1: 10K PD=2: 100K PD=3: 1M	 PA2 & PB0 default pull up 10KΩ PA0 default pull Down 10KΩ USBDM & USBDP default pull Down 15KΩ 		
USBDP	1.5K	15K	4、internal pull-up /pull-down resistance accuracy ±20%		
USBDM	180K	15K	12070		

3.5 Audio DAC Characteristics

Audio high voltage mode

Table 3-5

Parameter	MODE	Min	Тур	Max	Unit	Test Conditions
Frequency Response		20		20k	Hz	Fin=1kHz/0dB
Output Swing	Single-ended		0.57		Vrms	Fs=44.1kHz
THD+N	Single-ended		-82		Jp.	B/W=20Hz~20kHz
S/N	Single-ended		91		dB	A-Weighted Filter
Noise Floor	Single-ended		16	6	uVrms	10k ohm loading

3.6 Audio ADC Characteristics

Audio high voltage mode

Table 3-6

Parameter	MODE	Min	Тур	Max	Unit	Test Conditions
Resolution				16	bits	
	Single-ended		0.85			Gain Level = 0
Marrimana Immut I aval	Single-chied		0.03		Vrms	Fin = 1kHz
Maximum Input Level	Differential		0.85		VIIIS	$F_S = 44.1 \text{kHz}$
	Differential		0.83			THD+N < 0.1%
SNR	Single-ended		93		dB	Gain Level = 0
SINK	Differential		95		ав	$F_S = 44.1 \text{kHz}$
THD+N	Single-ended		-80			Fin = 1kHz,Maximum Input
InD⊤N					dB	$B/W = 20Hz\sim20kHz$
	Differential		-85			A-Weighted Filter



3.7 APA Characteristics

Table 3-7

Table 3-7									
Parameter	VPWR	Min	Тур	Max	Unit	Tes	t Conditions		
			2.30			$R_L=10K$			
	3.7V		1.76			$R_L=8\Omega$			
0.4.45			1.47		3.7	$R_L=4\Omega$	Differential mode		
Output Swing			1.43		Vrms	R _L =10K	Fin=1kHz/0dB B/W=20Hz~20kHz		
	2.4V		1.03			$R_L=8\Omega$			
			0.77			$R_L=4\Omega$			
			99			R _L =10K	ß.		
	3.7V		96			$R_L=8\Omega$			
SNR			96		dB	$R_L=4\Omega$	Differential mode Fin=1kHz/0dB B/W=20Hz~20kHz A-Weig hted Filter		
	2.4V		99			R _L =10K			
			96			$R_L=8\Omega$			
			94			$R_L=4\Omega$			
			-73			R _L =10K			
	3.7V		-38			$R_L=8\Omega$	Ç		
THD+N			-31		dB	$R_L=4\Omega$			
			-73			R _L =10K			
	2.4V	Blov	-36			$R_L=8\Omega$			
			-30	*		$R_L=4\Omega$			
	3.7V		0.38			$R_L=8\Omega$	Differential mode Fin=1kHz/0dB		
Output power	The state of the s		0.54		W	$R_L=4\Omega$			
	2.4V	V-	0.13			$R_L=8\Omega$			
			0.14			$R_L=4\Omega$			



3.8 BT Characteristics

3.8.1 Transmitter

1M Data Rate

Table 3-8-1-1

1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1						
Paramete	Parameter		Тур	Max	Unit	Test Conditions
RF Transmit Power			0	6	dBm	
RF Power Contro	ol Range		20		dB	
	+2MHz		-40			
In-band spurious	-2MHz		-40		dBm	25°C Power Supply VPWR=3.7V 2440MHz
Emissions	+3MHz		-45			
	-3MHz		-45			4 Layers Board
∆fl avg			250		KHz	(4)
△f2 min			210		KIIZ	0
rianglef2 avg/ $ riangle$ f1 avg			1		.0	

2M Data Rate

2M Data Rate Table 3-8-1-2						
Paramete	er	Min	Тур	Max	Unit	Test Conditions
	+4MHz		-40		- dBm	
	-4MHz		-40			
Adjacent Channel Transmit Power	+5MHz		-40			25℃ Power Supply VPWR=3.7V 2440MHz 4 Layers Board
	-5MHz		-40			
	+6MHz		-40			
	-6MHz		-40			
rianglefl avg			500		KHz	
△f2 min			430		KIIZ	
△f2 avg/△f1 avg			1.1			



3.8.2 Receiver

1M Data Rate

Table 3-8-2-1

Paramete	Parameter		Тур	Max	Unit	Test Conditions
Sensitivity		-98	-97		dBm	
Co-channel Interferen	ice Rejection		5		dB	
	+1MHz		-15			25℃
	-1MHz		-20			Power Supply
Adjacent Channel	+2MHz		-35		150	VPWR=3.7V 2440MHz
Interference Rejection	-2MHz		-25		dB	4 Layers Board
	+3MHz		-30			
	-3MHz		-25		5	14

2M Data Rate

Table 3-8-2-2

Paramete	r	Min	Тур	Max	Unit	Test Conditions
Sensitivity		-95	-94		dBm	
Co-channel Interferen	ce Rejection		3	/.C	dB	
Adjacent Channel Interference Rejection	+1MHz -1MHz +2MHz -2MHz +3MHz		6 6 -20 -16 -25		dB	25°C Power Supply VPWR=3.7V 2440MHz 4 Layers Board



3.9 ESD Protection

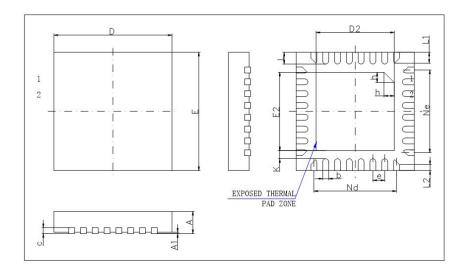
Table 3-9

Parameter	Тур.	Test pin	Reference standard
Human Body Mode	±4KV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±200V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±500V	All pins	JEDEC EIA/JESD22-C101F
Lotale vie	±200mA	All GPIO pins	JEDEC STANDARD NO.78E
Latch up	1.5xVopmax	All power pins	JEDEC STANDARD NO./8E

Note: 1.5xVopmax = 1.5 times maximum operating voltage.

4 Package Information

4.1 QFN32_4×4mm



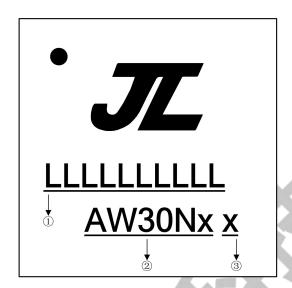
SYMBOL	MILLIMETER				
SYMBOL	MIN	NOM	MAX		
	0.70	0.75	0.80		
A	0.80	0.85	0.90		
	0.85	0.90	0.95		
A1	0	0.02	0.05		
ь	0.15	0.20	0.25		
c	0.18	0.20	0.25		
D	3.90	4.00	4.10		
D2	2.50	2.65	2.80		
e	0.40BSC				
Nd	2.80BSC				
Е	3.90	4.00	4.10		
E2	2.50	2.65	2.80		
Ne		2.80BSC			
K	0.20	-	-		
L	0.35	0.40	0.45		
L1	0.30	0.35	0.40		
L2	0.15	0.20	0.25		
h	0.30	0.35	0.40		
L/F 载体尺寸 (mil)	112*112				



Figure 4-1 AW306A Package



5 IC Marking Information



- ① LLLLLLLLL: Production Batch
- ② AW30Nx: Chip Model
- 3 Built-in flash size
 - 0: No Flash Memory
 - 2: 2Mbit Flash
 - 4: 4Mbit Flash
 - 8: 8Mbit Flash
 - 6: 16Mbit Flash
 - 3: 32Mbit Flash



6 Solder-Reflow Condition

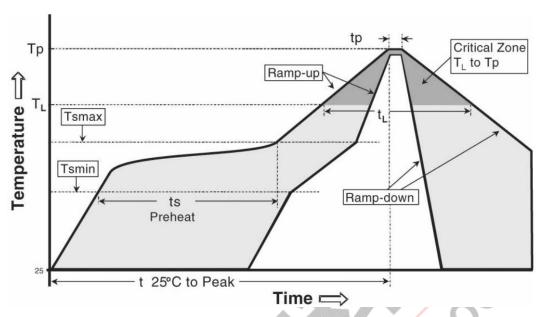


Figure 6-1 Classification Reflow Profile

Classification Profiles

Table 6-1

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
	Temperature Min (T _{smin})	rature Min (T _{smin})	
Preheat/	Temperature Max (T _{smax})	150℃	200℃
Soak	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds
Average ra	amp-up rate $(T_{smax}$ to $T_p)$	3°C/second max	3°C/second max
Liquidous temperature (T _L)		183℃	217℃
Time (t _L) maintained above T _L		60-150 seconds	60-150 seconds
Peak package body temperature (Tp)		See Table 5-2	See Table 5-3
Time within 5°C of actual Peak Temperature (tp) ²		10-30 seconds	20-40 seconds
Ramp-down rate (Tp to TL)		6°C/second max	6°C/second max
Time 25℃	to peak temperature	6 minutes max	8 minutes max

Note 1: All temperatures refer to topside of the package, measured on the package body surface.

Note 2: Time within 5° C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" minimum and "user" maximum.

<u>SnPb - Classification Temperature</u>

Table 6-2

Package Thickness	Volume mm³ < 350	Volume mm³ ≥ 350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5℃	225 +0/-5℃



Pb-free - Classification Temperature

Table 6-3

Name of Substitution Temperature					
Package	Volume mm ³	Volume mm ³	Volume mm ³		
Thickness	< 350	350 - 2000	> 2000		
< 1.6mm	260℃	260℃	260℃		
1.6 mm - 2.5mm	260℃	250℃	245℃		
> 2.5mm	250℃	245℃	245℃		

^{*}Tolerance: The device manufancturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

7 Revision History

Date	Revision	Description
2023.12.08	V1.0	Initial Release
2023.12.14	V1.1	Update APA Characteristics Update BT Characteristics